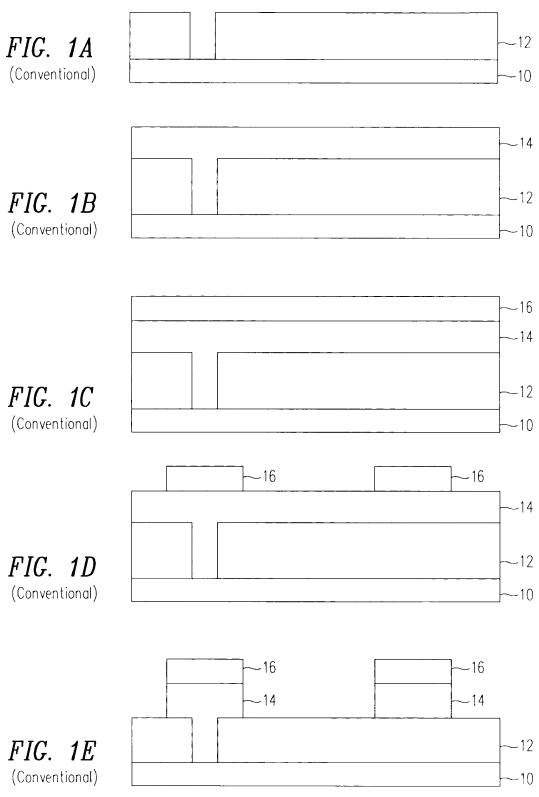


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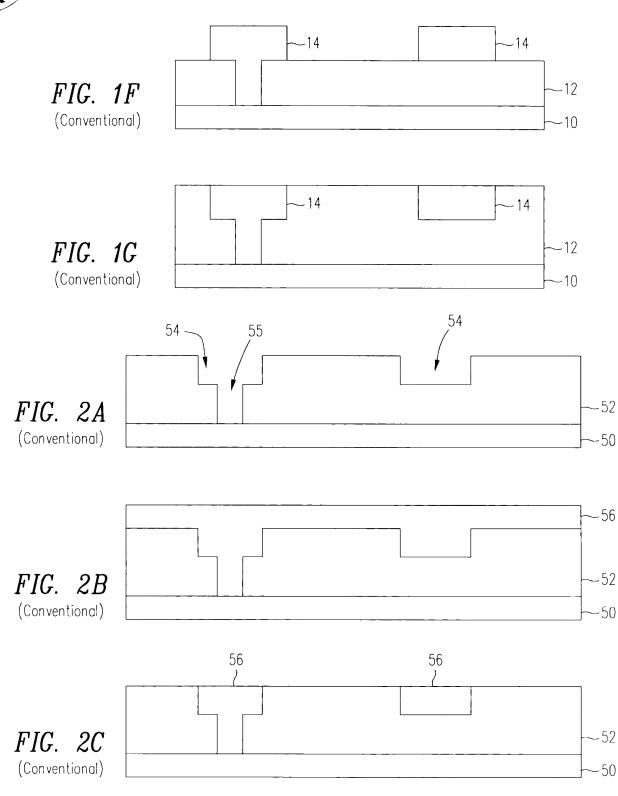
1/4





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Method of Measuring Dishing Jaime Paris Application No: 09/578,798 Docket No. NAN040 US

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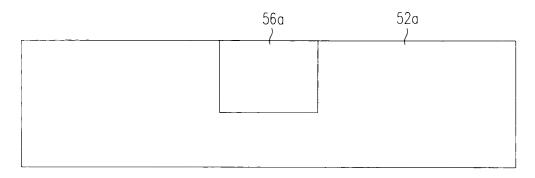


FIG. 3

(Conventional)

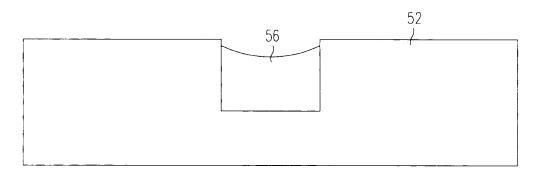


FIG. 4 (Conventional)

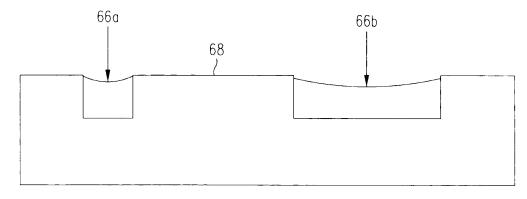


FIG. 5



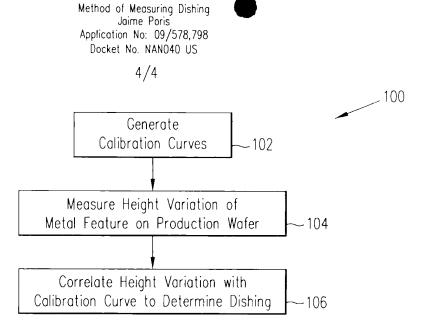


FIG. 6

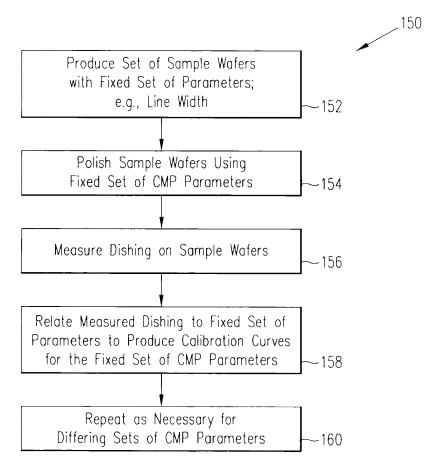


FIG. 7



PATTERNED AND ETCHED DIELECTR
ALUMINUM DEPOSITION
PHOTORESIST DEPOSITION
EXPOSURE AND DEVELOP
ALUMINUM ETCHING
PHOTORESIST REMOVAL
FIGURE 1



DIELECTRIC
ETCHED
AND
PATTERNED

DIFFUSION BARRIER, NUCLEATION LAYER AND COPPER DEPOSITION COPPER, NUCLEATION LAYER AND DIFFUSION BARRIER CMP

FIGURE 2



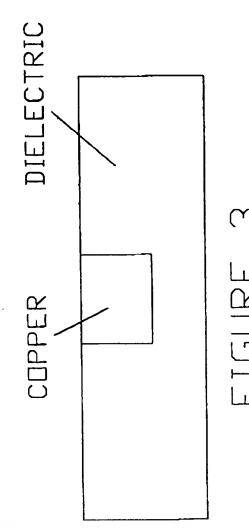


FIGURE 3



